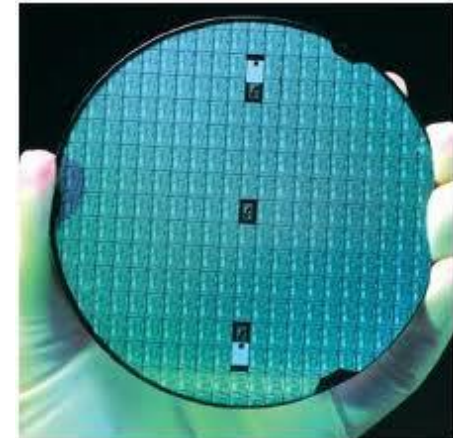
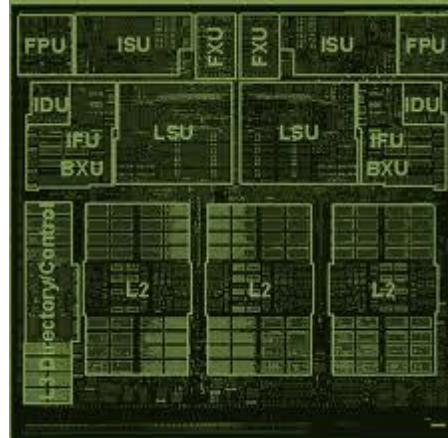
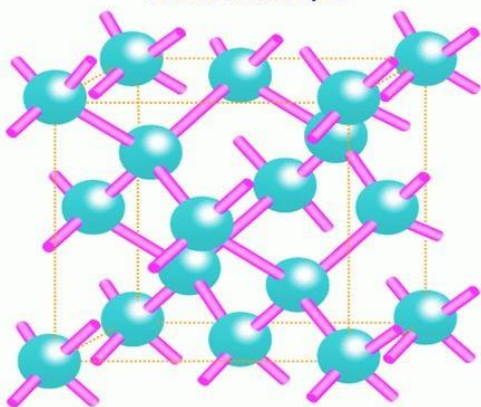


Structure of silicon crystal



ECE 225

High Speed Digital IC Design

Lecture 1

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Electrical and Computer Engineering
University of California, Santa Barbara
E-mail: kaustav@ece.ucsb.edu

Course Description....

- ❑ Advanced CMOS VLSI design concepts
- ❑ Nanometer scale issues in VLSI
 - CMOS scaling, nanoscale issues including variability, power and thermal management, interconnects, reliability
- ❑ Emerging Technologies for VLSI
 - Classical and non-classical CMOS
 - Non-Si devices and interconnect technologies

Textbook and References

❑ Recommended (Reference) Books

- Modern VLSI Devices by Y. Taur and T. Ning, Cambridge Univ. Press, Second edition, 2009.
- Design of High-Performance Microprocessor Circuits, Chandrakasan, Bowhill and Fox (Eds.), IEEE Press, 2001.
- Emerging Nanoelectronics: Life With and After CMOS, Eds. A. M. Ionescu and K. Banerjee, Springer, 2004.

❑ Basic References

- ECE 124A Fall 2014 Course Notes
- http://www.ece.ucsb.edu/courses/ECE225/225_S16Banerjee/
CMOS VLSI Design: A Circuits and Systems Perspective (3rd Edition), Neil H. E. Weste and David Harris, Addison Wesley, © 2005.

❑ Other Reference Materials

- To be posted on the class web site:
<http://tinyurl.com/ECE225S16>

Prerequisites

- ❑ ECE122A or equivalent is recommended
- ❑ Basic Digital Circuit Analysis (both analytical and simulation based)
- ❑ Other
 - Fundamentals of Circuits
 - Resistance, capacitance, inductance, power/energy
 - Fundamentals of Electronic Devices

Preparation for the course

❑ Computing Environment and Tools

- Setup computer account, and the computing environment
- Familiarize with the schematic and layout editors
- Familiarize with the parasitic extractor and circuit simulator

❑ Theory

- Review ECE 122A Lecture Notes

❑ Projects

- You should start formalizing your project ASAP
 - **Certainly by Week 3...**
- **Must work on your own!!**

Review-I: Basic Understanding of the MOSFET

- *Band Diagrams*
- *I-V curves*
- *Static/dynamic behavior*
- *Parameters (process, temperature, voltage) that impact device behavior*
- *Impact on circuit parameters (delay, power, NM)*

Review-II: Implementation & Sizing of Complex Gates...

- *Described as: Boolean function, K-map, Truth Table, or propositions*
- *Sizing of gates to get equivalent inverter size (based on worst case delay) ---with and without considering internal capacitances*

Review-III: Circuit Level Implementation Choices for Complex gates

- *Implement a function F with*
 - *Static CMOS*
 - *Pass Transistors or transmission-gates*
 - *Pseudo-NMOS*
 - *Dynamic Logic (including Domino)*
- *Pros and Cons of each of the methods (in terms of delay, power, area, noise margins etc.)*

Review-IV: Elmore Delay

Know how to apply Elmore delay to find the delay between any two points in a:

- *Given RC tree*
- *Given topology of gates (find their equivalent RC...)*

Review-V: Optimization of a Design

- *Optimizing a design in terms of delay and power dissipation*
- *Choosing optimal number and sizes to minimize the delay for*
 - *Inverter chain*
 - *Gates (Logical Effort)*
- *Trade-off between delay and power dissipation*

Review-VI: Sequential Circuits

- *Design of foreground memory elements*
 - *Latches*
 - *Filp Flops*
- *Timing parameters (understand in terms of circuit design and topology)*
 - *setup time*
 - *hold time*
 - *clock skew*

Review-VII: Semiconductor Memories

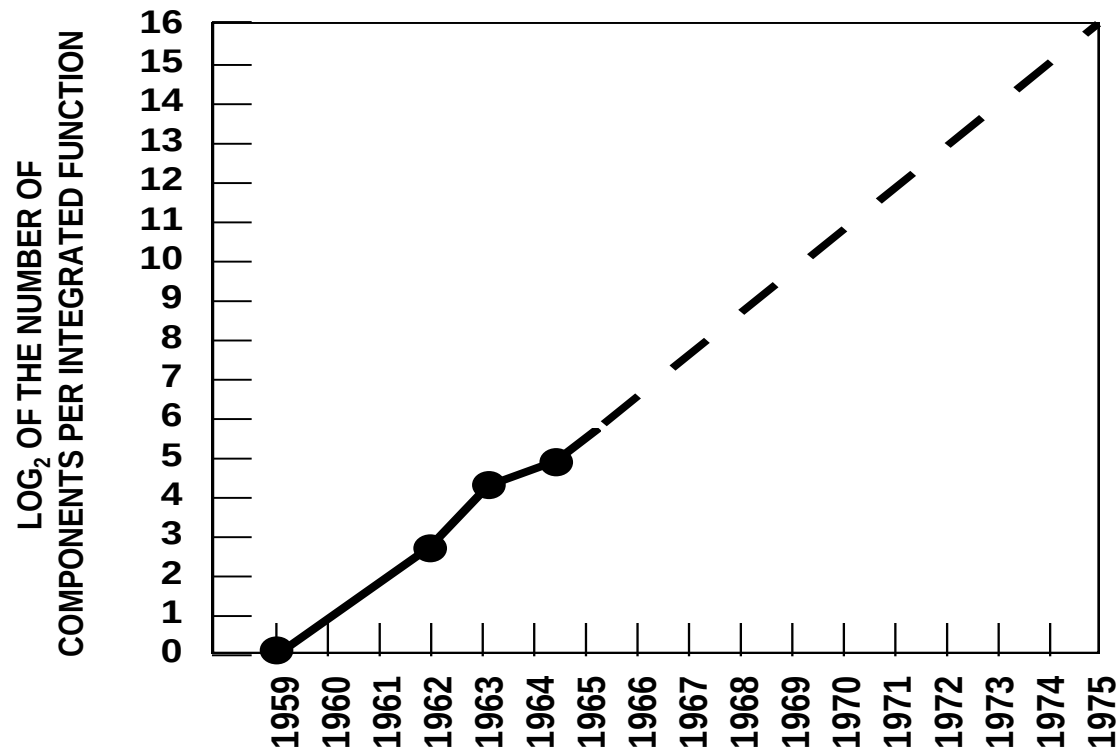
- *Basic Types*
- *SRAM (circuit level implementation...., read and write operations, sizing issues)*
- *DRAM (circuit level implementation, read and write operations, processing issues)*

Nanometer Scale CMOS Issues & Emerging Technologies for VLSI

Introduction

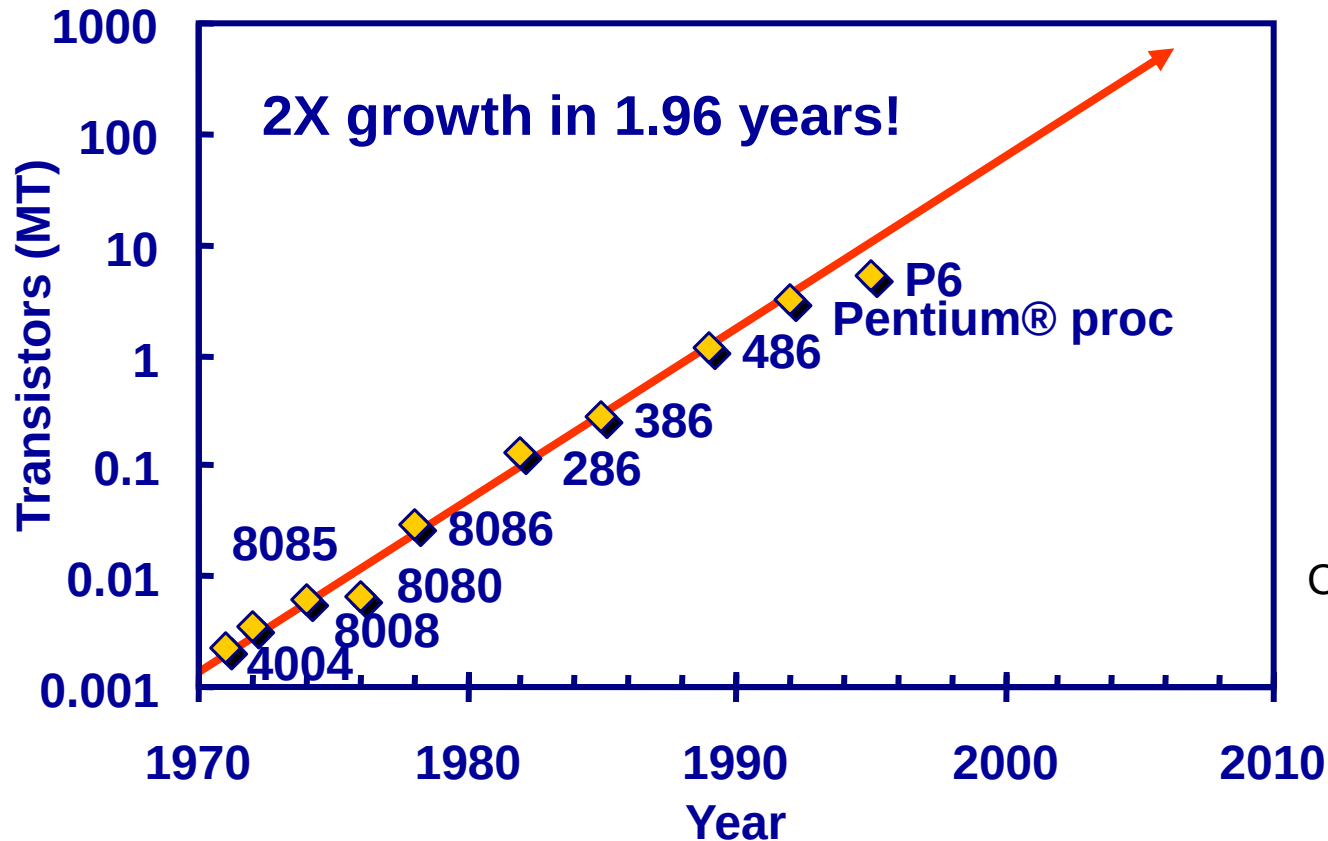
- ❑ Why is designing digital ICs different today than it was before?
- ❑ Will it change in future?

Moore's Law



Electronics, April 19, 1965.

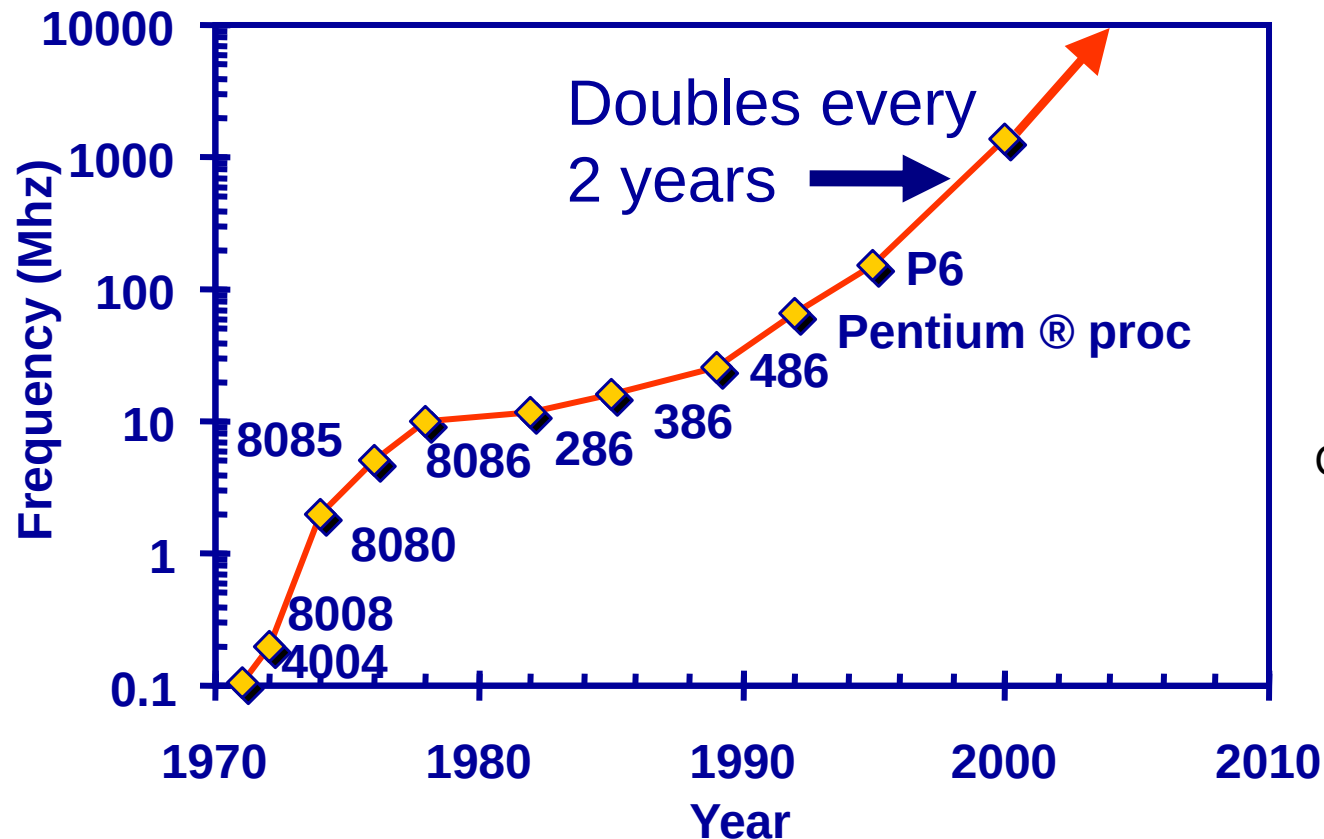
Moore's law in Microprocessors



Courtesy, Intel

Transistors on Lead Microprocessors double every 2 years

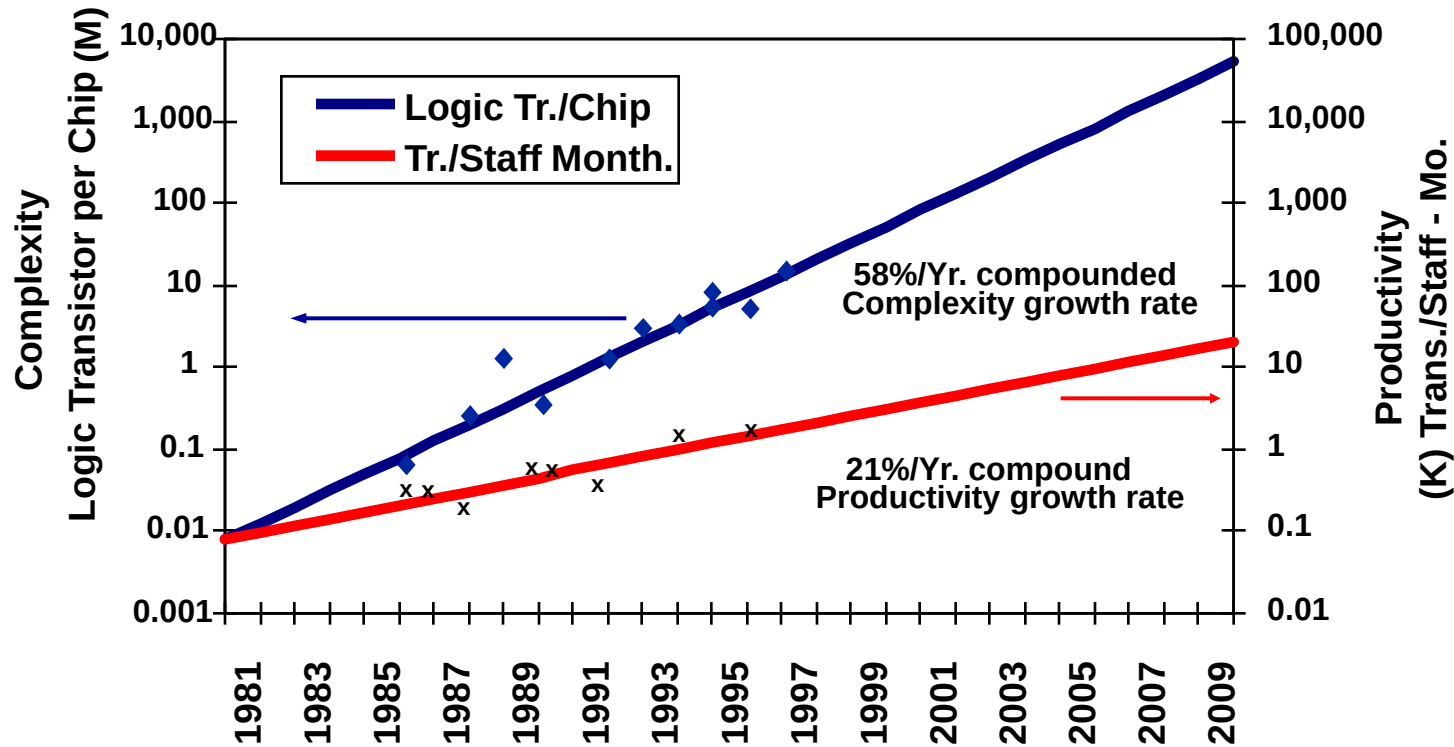
Frequency



Courtesy, Intel

Lead Microprocessors frequency doubles every 2 years

Productivity Trends



Source: Sematech

Complexity outpaces design productivity

Courtesy, ITRS Roadmap

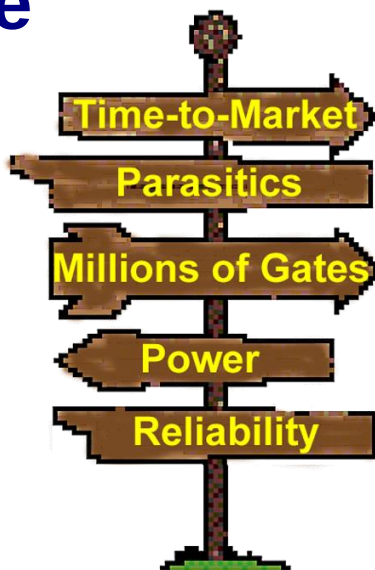
Challenges in Digital Design

$\propto$ Nanometer Scale

“Nanoscale Problems”

- Ultra-Short channel devices
- Interconnect issues
- Noise, Crosstalk
- Reliability
- Variability
- Manufacturability
- Power dissipation

Everything Looks a Little Different



?

$\propto$ 1/nanoscale

“Macroscopic Issues”

- Time-to-Market
- Millions of Gates
- High-Level Abstractions
- Reuse & IP: Portability
- Predictability
- etc.

...and There's a Lot of Them!

VLSI Design Metrics

- ❑ How to evaluate performance of a digital circuit (gate, block, ...)?
 - Cost
 - Reliability
 - Scalability
 - Robustness
 - Speed (delay, operating frequency)
 - Power dissipation
 - Energy to perform a function

VLSI Designer's Tasks

- ❑ Job of VLSI designer: design a circuit block to meet one or more objectives:
 - Maximize speed, performance
 - Minimize power consumption
 - Minimize area
 - Increase noise immunity (robustness)
- ❑ How?
 - Choice of circuit style (static, dynamic, etc)
 - Circuit design, transistor sizing
 - Interconnect design, efficient layout

VLSI Design Challenges

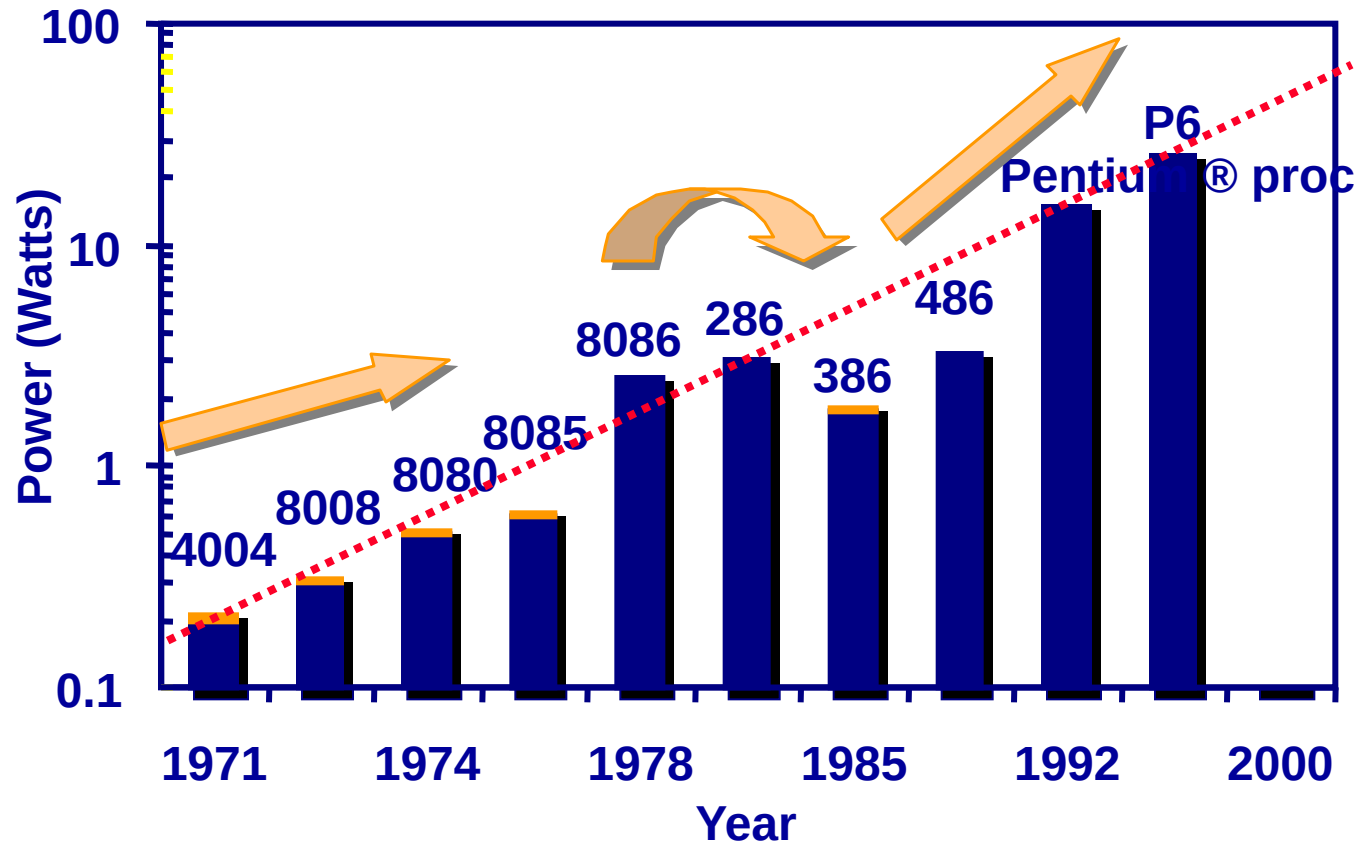
- Power consumption, especially leakage power. Also affects chip cooling and packaging.
- Noise issues, as transistors and wires move closer together.
- Clocking: distributing high-frequency clock with minimum of skew (difference in clock arrival time between points on a chip)
- Reliability issues such as electromigration, NBTI, TDDB, and ESD

Variability affects all of the above.....

VLSI Design Challenges (Cont'd)

- **Scaling:** continue to make transistors smaller. Why? Smaller transistors are faster, can put more transistors on a die
- Scaling related challenges....
- **Integration:** combining large VLSI systems to form a “system-on-a-chip”
 - Design for reuse
 - Design for testability
 - Advanced CAD tools required

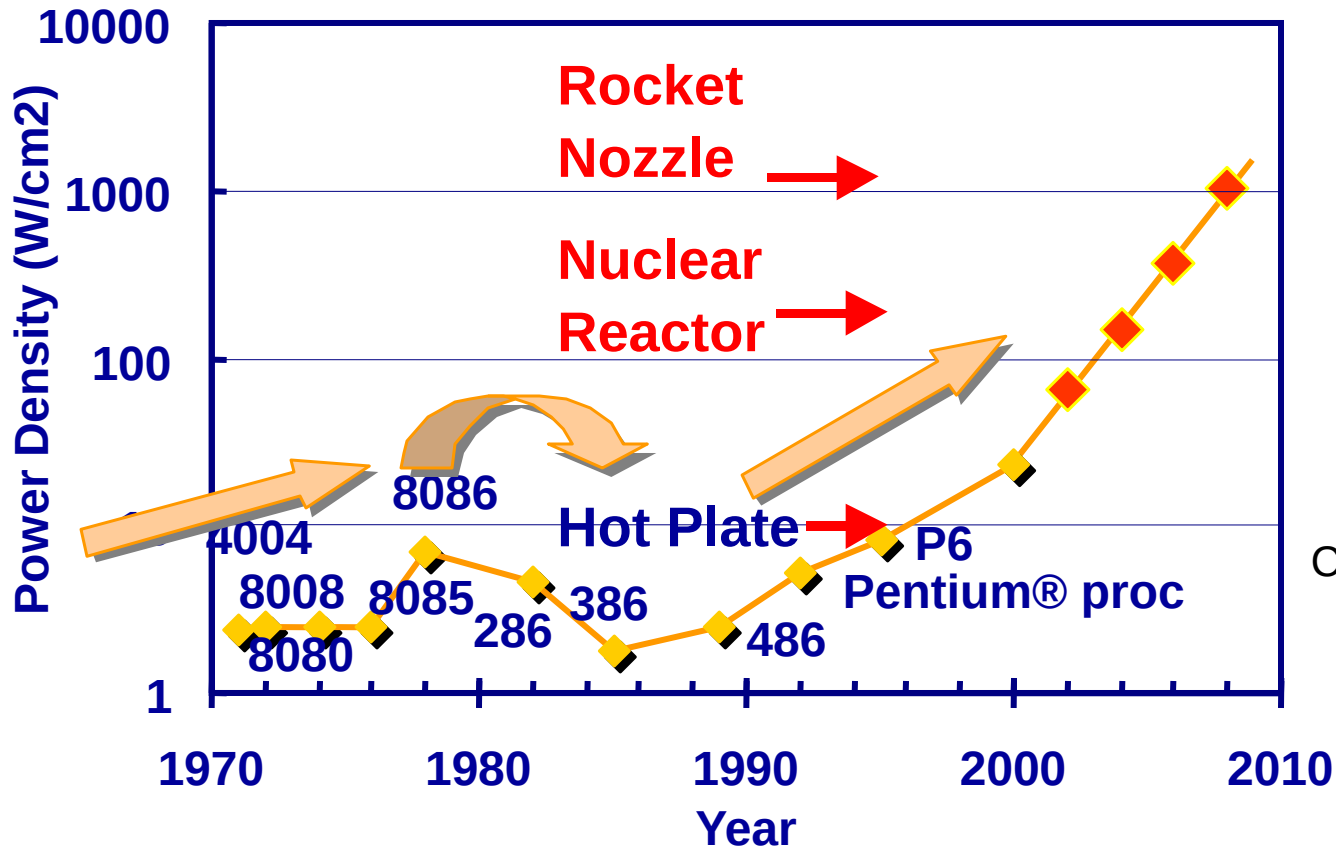
Power Dissipation



Courtesy, Intel

Lead Microprocessors power continues to increase

Power Density



Courtesy, Intel

Power density too high to keep junctions at low temp

Not Only Microprocessors....

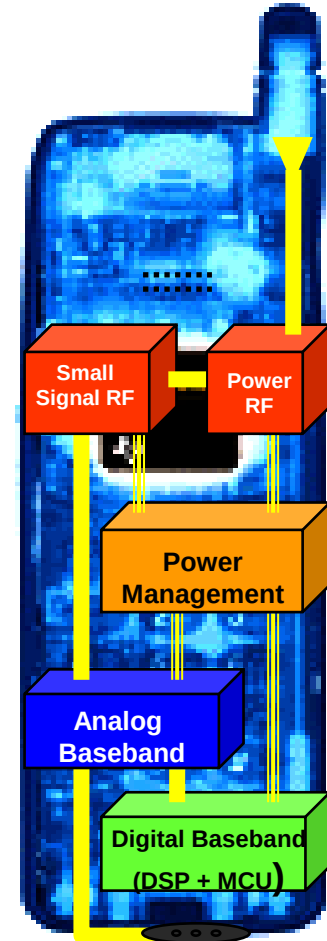
Cell
Phone



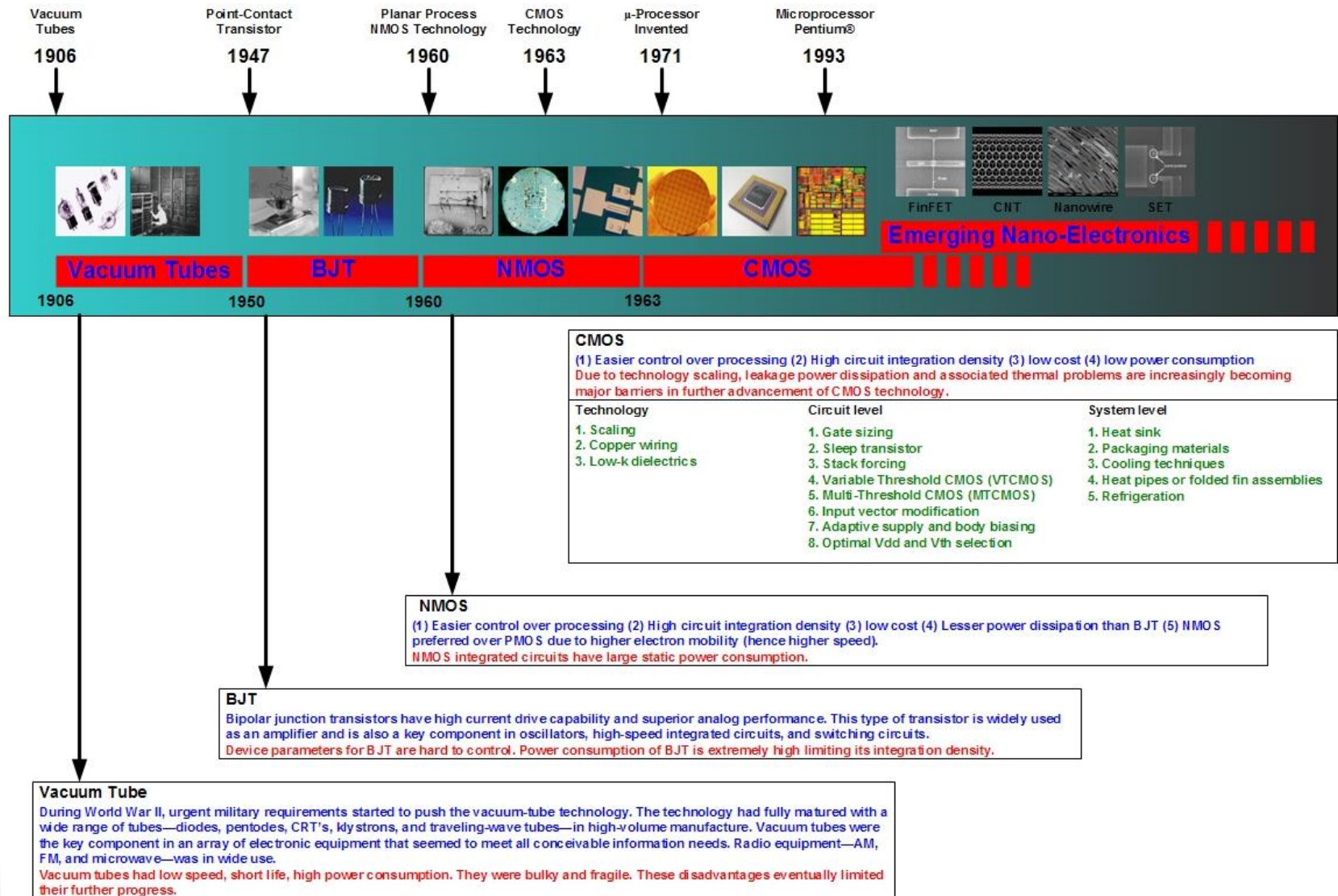
**Digital Cellular Market
(Phones Shipped)**

	1996	1997	1998	1999	2000
Units	48M	86M	162M	260M	435M

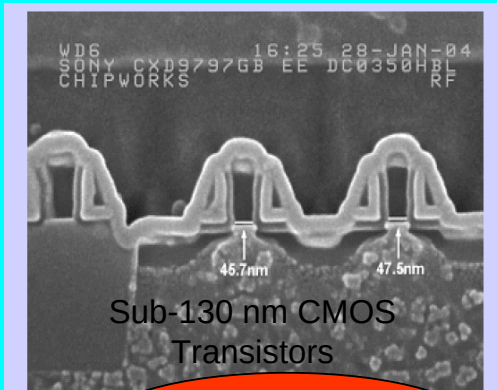
(data from Texas Instruments)



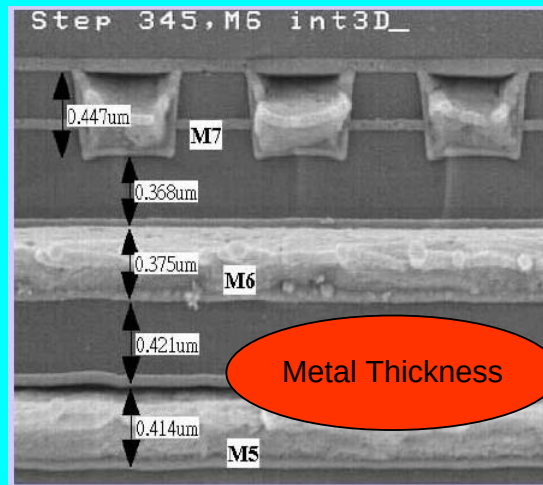
Historical Perspective....



Process, Temperature and Voltage Variations

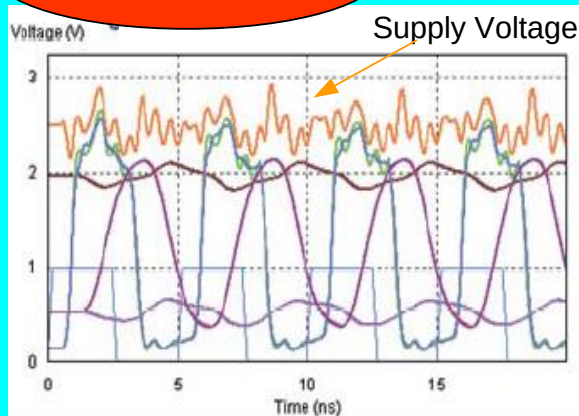


Transistor channel length

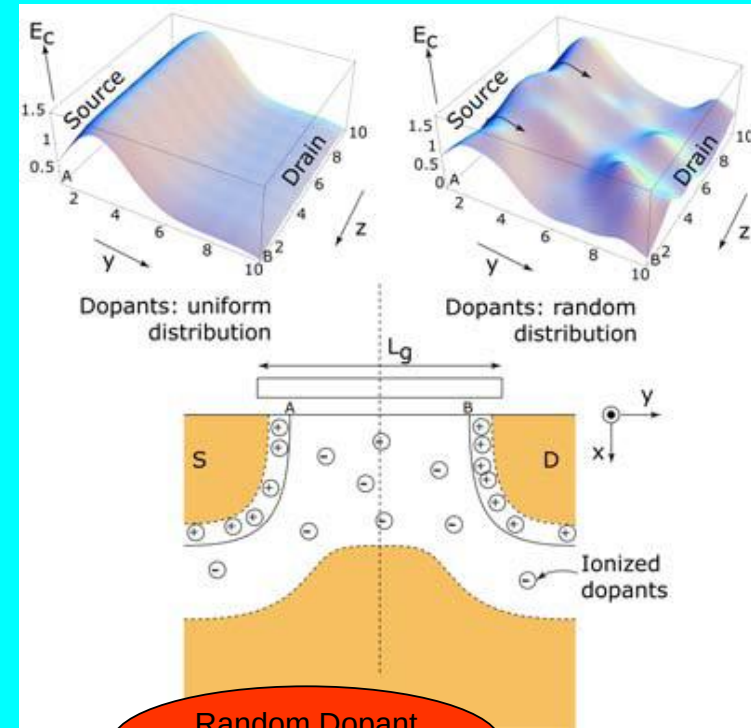
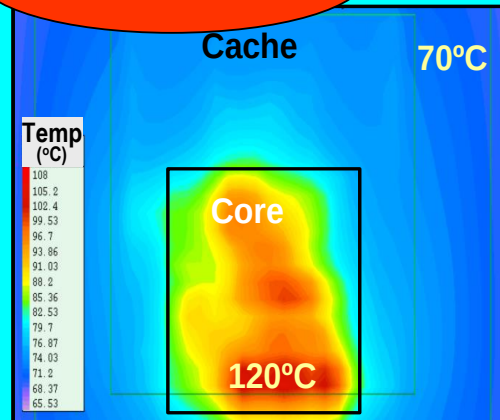


Metal Thickness

Power Supply Voltage



Chip Temperature

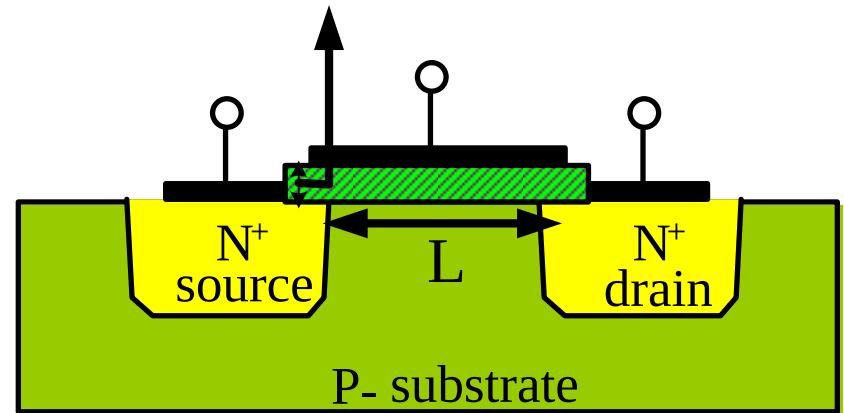


Random Dopant Fluctuations

Key Parameter Variations

■ Within-die Parameter Variations

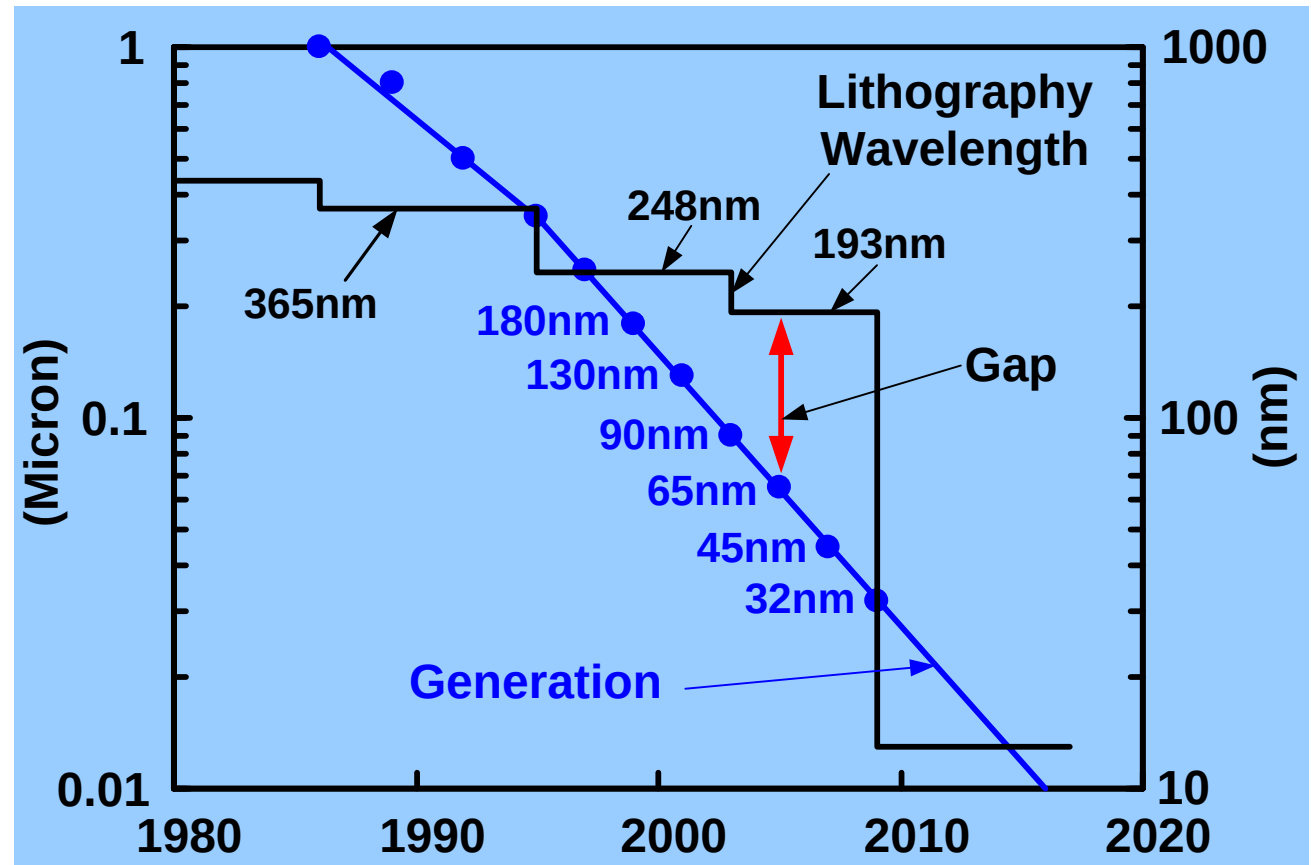
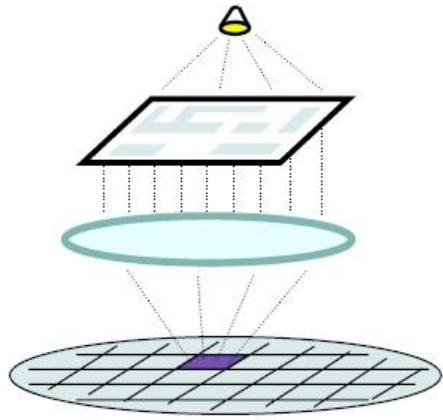
- Channel Length (L)
- Oxide Thickness (t_{ox})
- Temperature (T)
- Supply Voltage (V_{dd})



■ Die-to-Die Parameter Variations

- Channel Length (L)
- Temperature (T)

Why Channel Length Variations are Increasing?

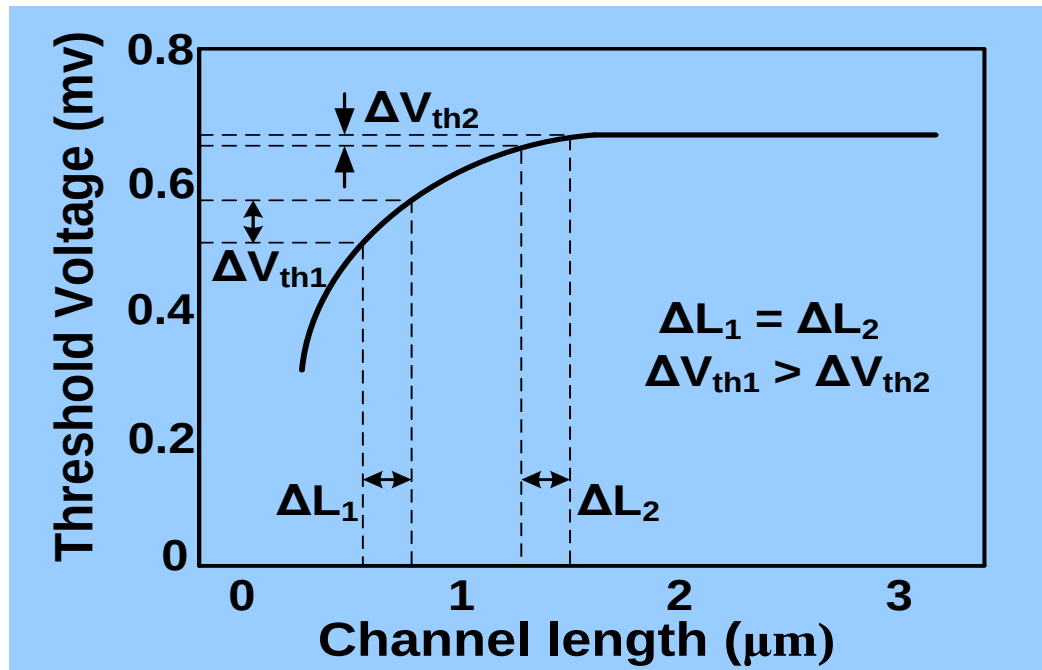


(S. Borkar et al. DAC2003)

- Minimum feature size is scaling faster than lithography wavelength
- Channel length exhibits significant amount of variations

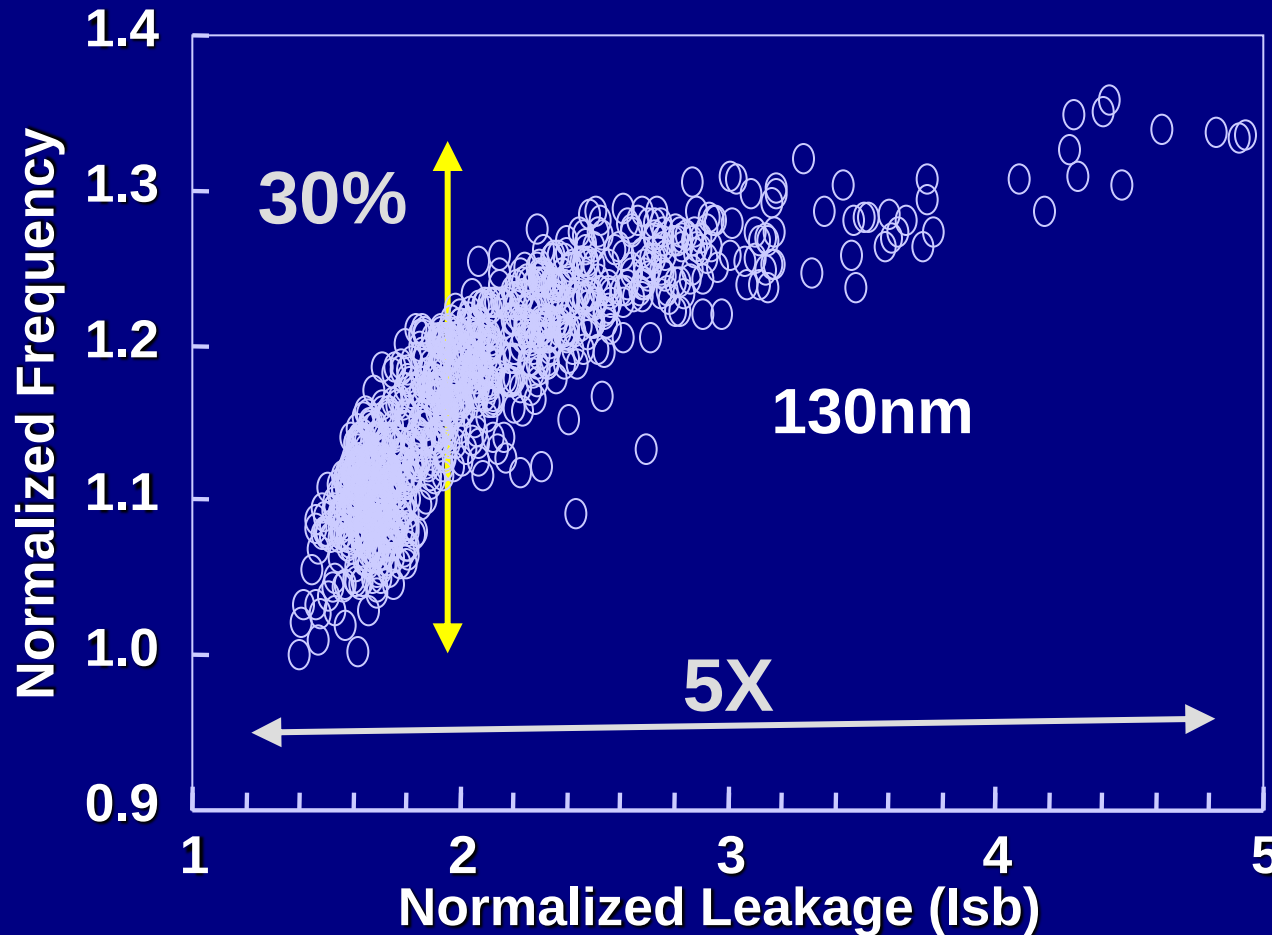
Impact of Device Scaling

Threshold voltage roll-off



- With technology scaling, the same amount of channel length variations result in greater variations in threshold voltage

Impact of Static Variations

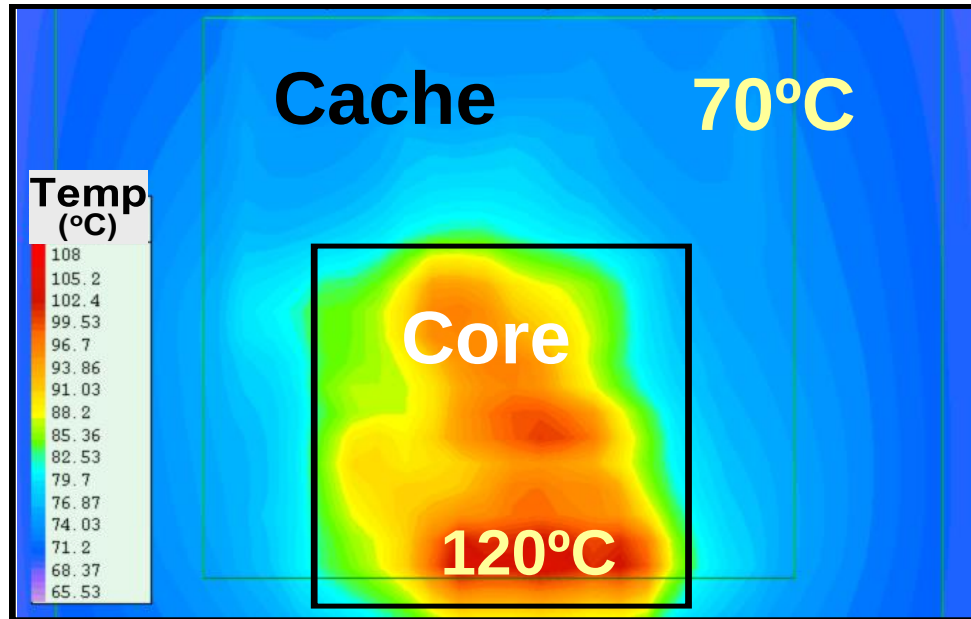


**Frequency
~30%**

**Leakage
Power
~5-10X**

Intel

Why On-Chip Temperature Variations are Increasing?

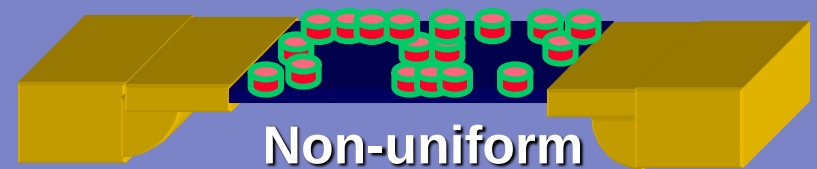
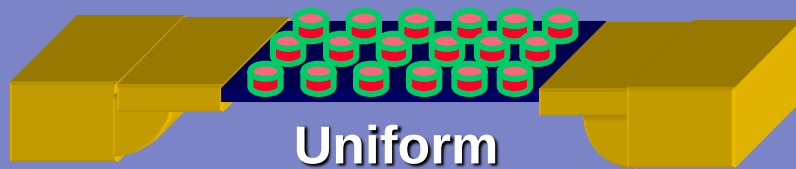
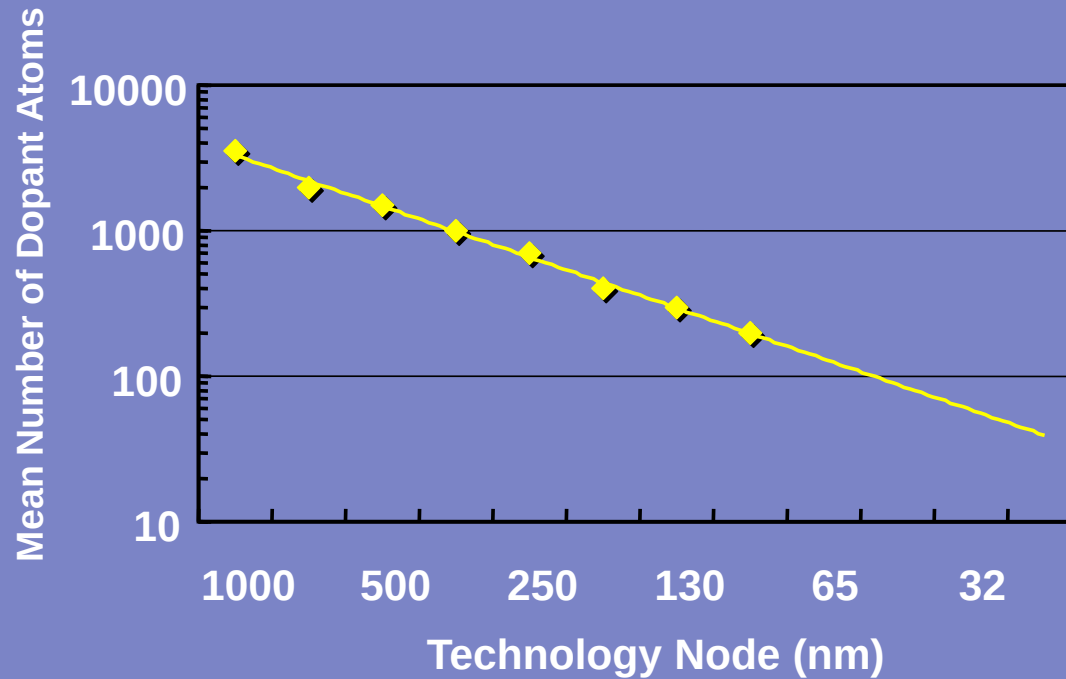


Temperature map of a high-performance microprocessor

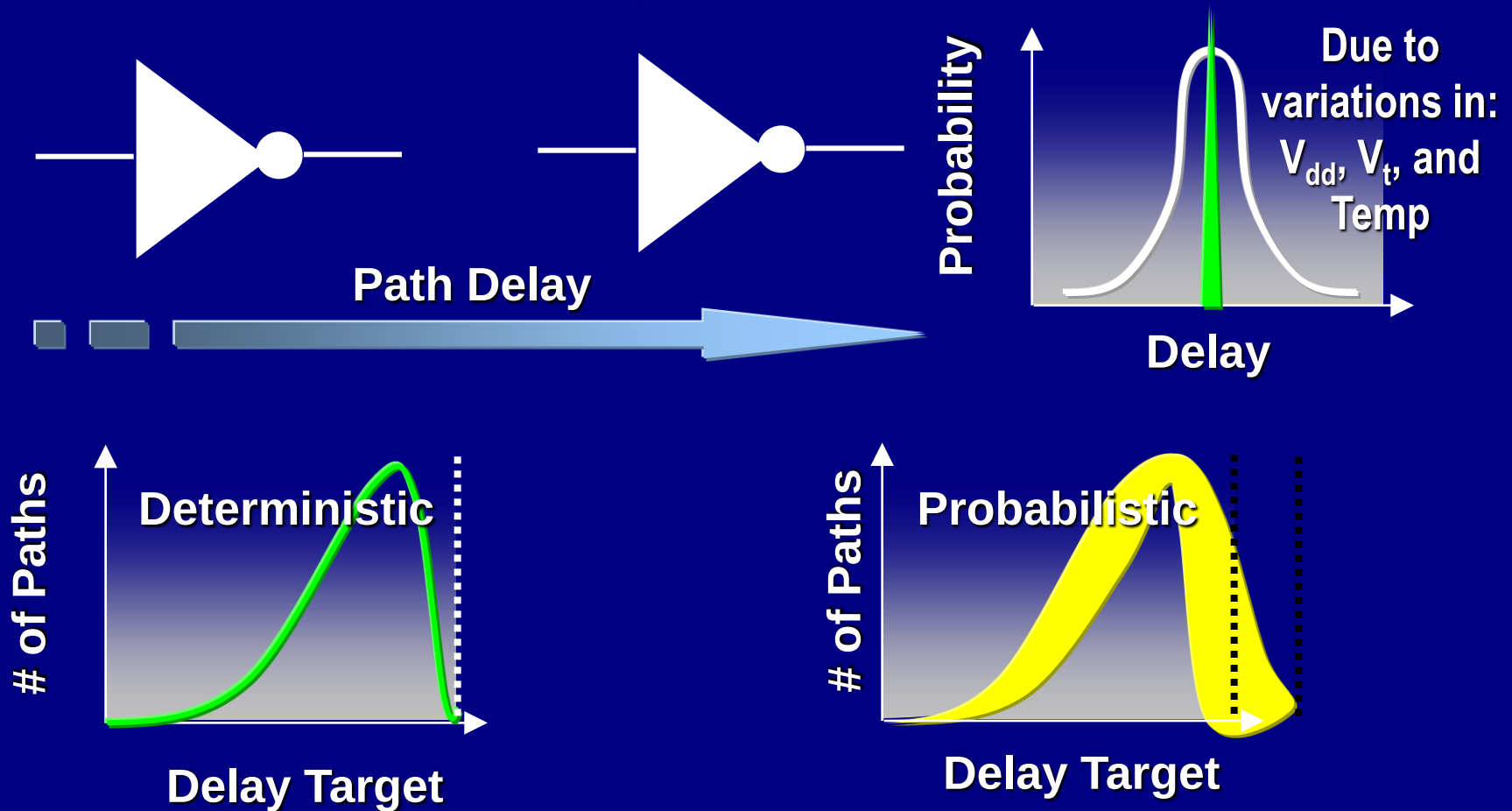
Courtesy of S. Borkar, Intel Corporation.

- Difference in power dissipation of various blocks
- Dynamic power management techniques such as clock gating
- Leakage power distribution

Random Dopant Fluctuations (Intrinsic)



Probabilistic Design



Deterministic design techniques inadequate in the future

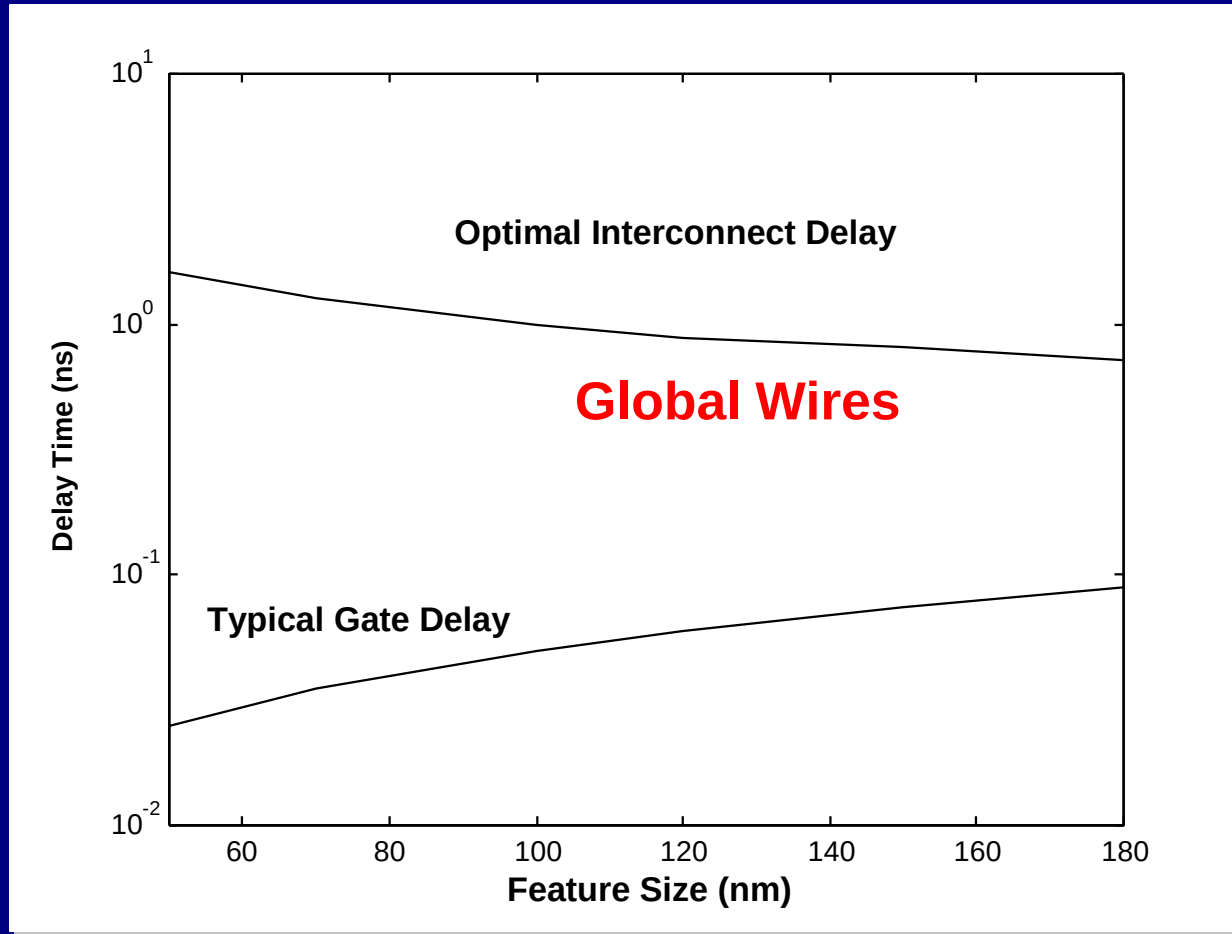
Shift in Design Paradigm

- ❑ Multi-variable design optimization for:
 - Yield and bin splits
 - Parameter variations
 - Active and leakage power
 - Performance

Today:
Local Optimization
Single Variable

Tomorrow:
Global Optimization
Multi-variable

IC performance is being dominated by interconnects



K. Banerjee et al., Proc. IEEE, May 2001.

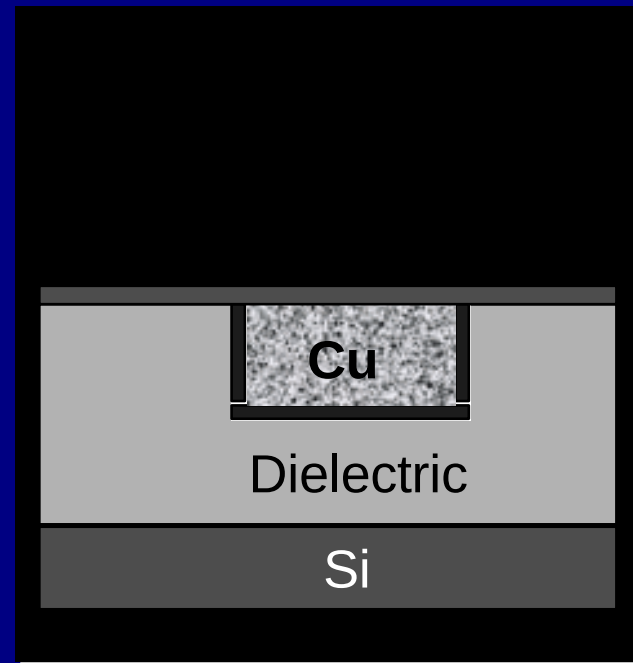
Cu Resistivity: Effect of Scaling

Effect of Cu Diffusion Barrier

- Barriers have higher resistivity
- Barriers can't be scaled below a minimum thickness

Effect of Grain Boundary Scattering

- e scattering from the G-bs
- increases effective resistivity

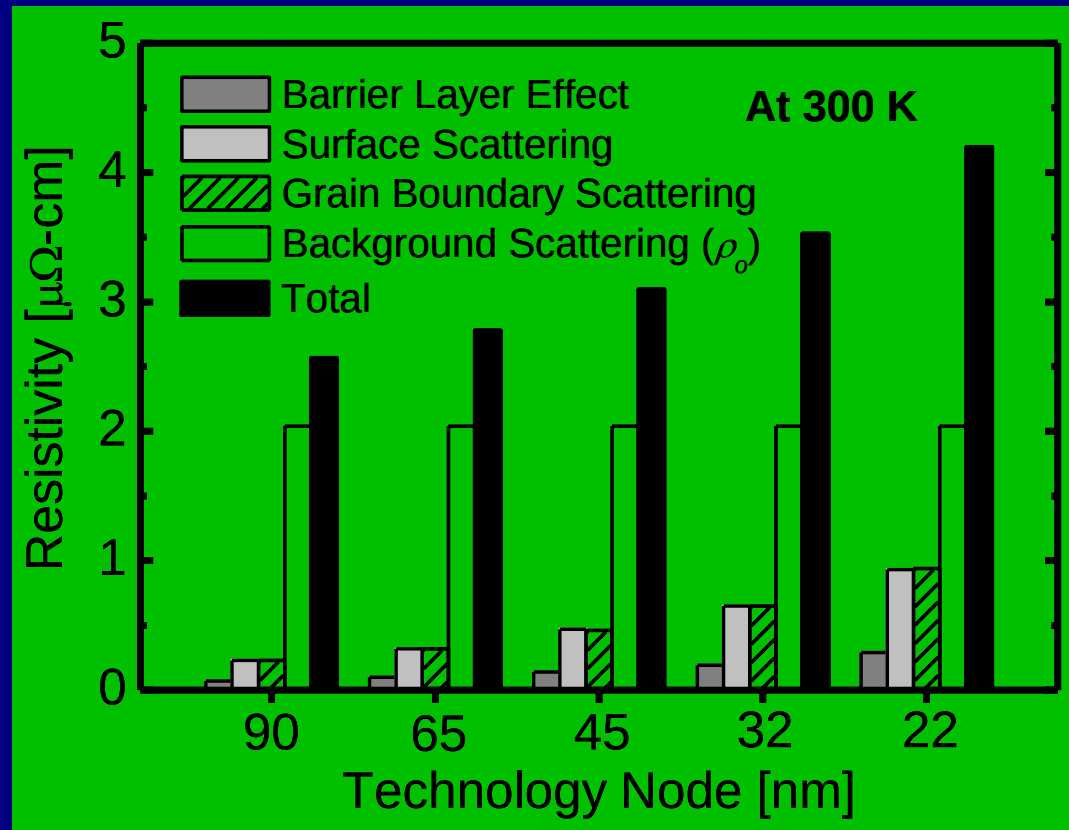


Effect of Electron Scattering

- e scattering from the surface
- further increase in effective resistivity

Problem is worse than anticipated in the ITRS roadmap

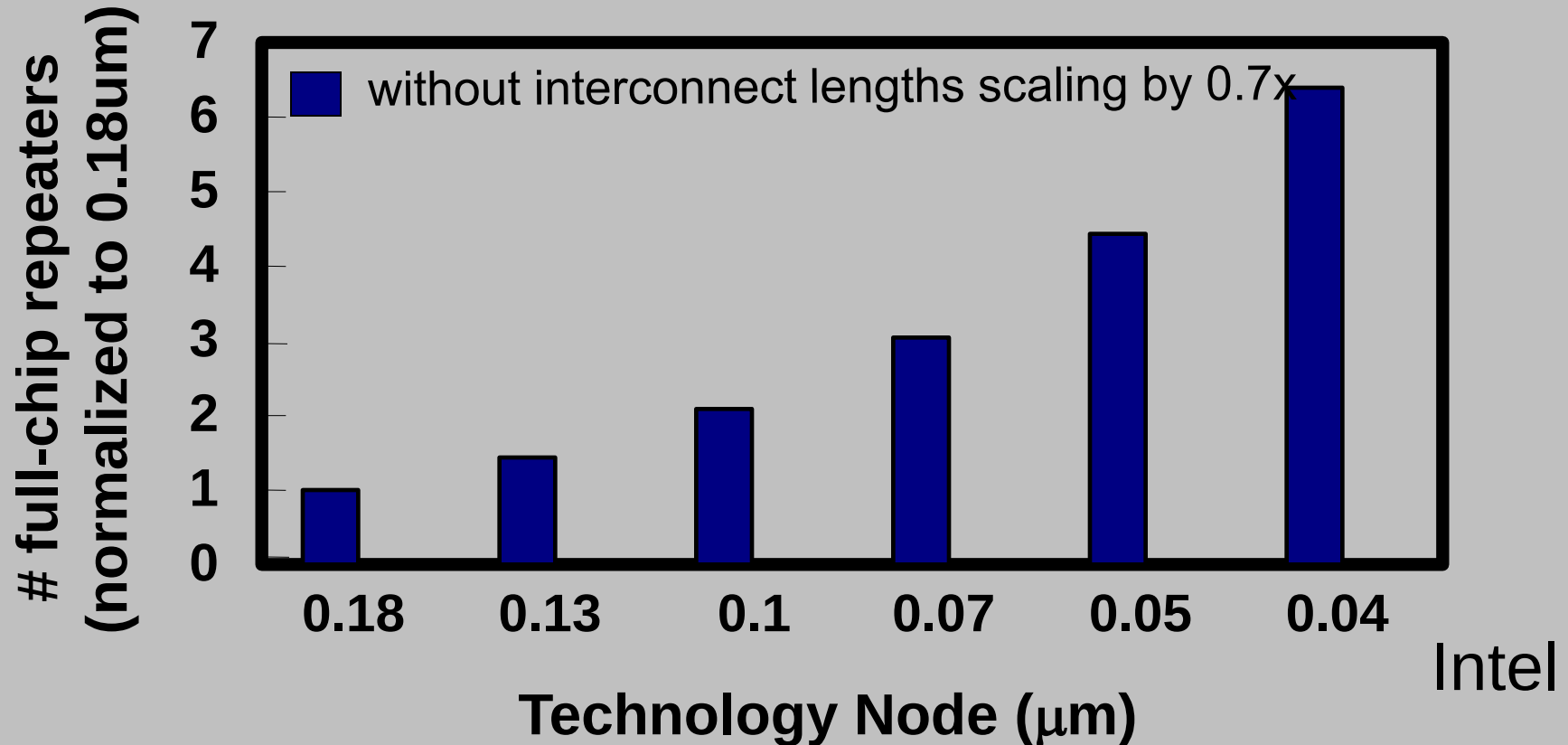
Cu Resistivity: Effect of Scaling



Im, Srivastava, Banerjee and Goodson, IEEE TED 2005.

Cu barrier layer, grain boundary and surface scattering leads to steep increase in Cu resistivity

Increasing Number of Repeaters



- Increase in Cu resistivity will cause increase in size and number of repeaters.....

Other Issues....

- Frequency of signals on interconnects is rising rapidly
- Frequency dependent impedance extraction is a major hurdle
 - Field solvers are unable to handle the complexity of VLSI interconnects
- Need to develop models for interconnect geometry dependent calculation of high frequency impedance
- Interconnect variability adds to the complexity of extraction....
- Situation is even more complex in 3-D ICs.....

Reliability Issues....affects design

- Electromigration in metal interconnects
- Self-heating issues
- Time-dependent dielectric breakdown
- Negative-Bias-Temperature-Instability(NBTI)
- Electrostatic discharge (ESD)

Nanoscale CMOS Problems and Solutions

- ❑ High E-field: mobility degradation
 - Use Ge or SiGe (introduce strain) and increase mobility
- ❑ Gate: tunneling and depletion
 - Use high-k dielectric, metal gate (work function engineering)
- ❑ Source/Drain: parasitic contact resistance
 - Use Silicides, Schottky S/D
- ❑ Channel: reduced $V_g - V_t$ causes reduction in I_{on} (electrostatics)
 - Use DG, FinFET or Tri-gate to retain gate control over channel, minimize I_{off}

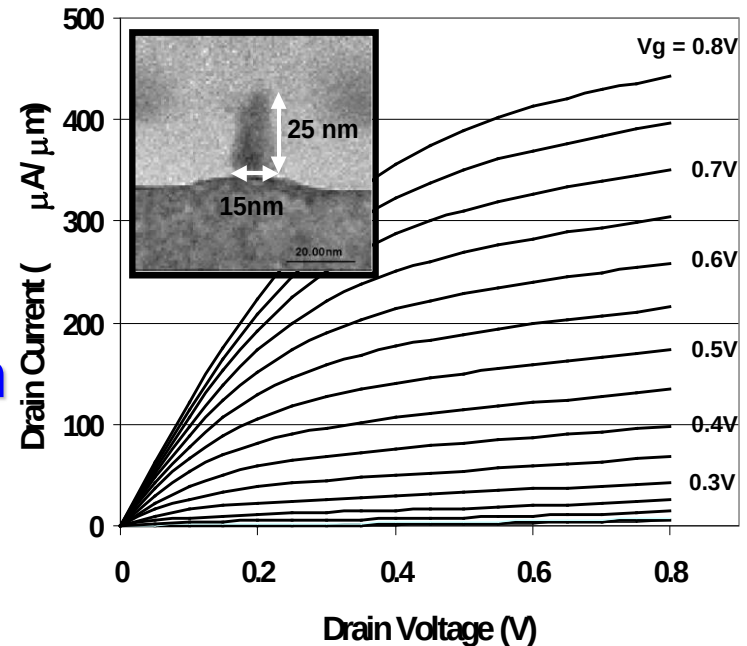
Pushing CMOS: the 10 nm wall?

- Smart engineering, new materials and evolutionary architectures have continuously pushed the CMOS limits...

$I_{\text{on}} > 700 \mu\text{A}/\mu\text{m}$
 $I_{\text{off}} < 1000 \text{ pA}/\mu\text{m}$
@ room temperature
low operating power logic

- **Key problems of sub-10 nm MOSFET**

- (i) electrostatic limits
- (ii) source-to-drain tunnelling
- (iii) carrier mobility
- (iv) process variations
- (v) static leakage
- (vi) power density

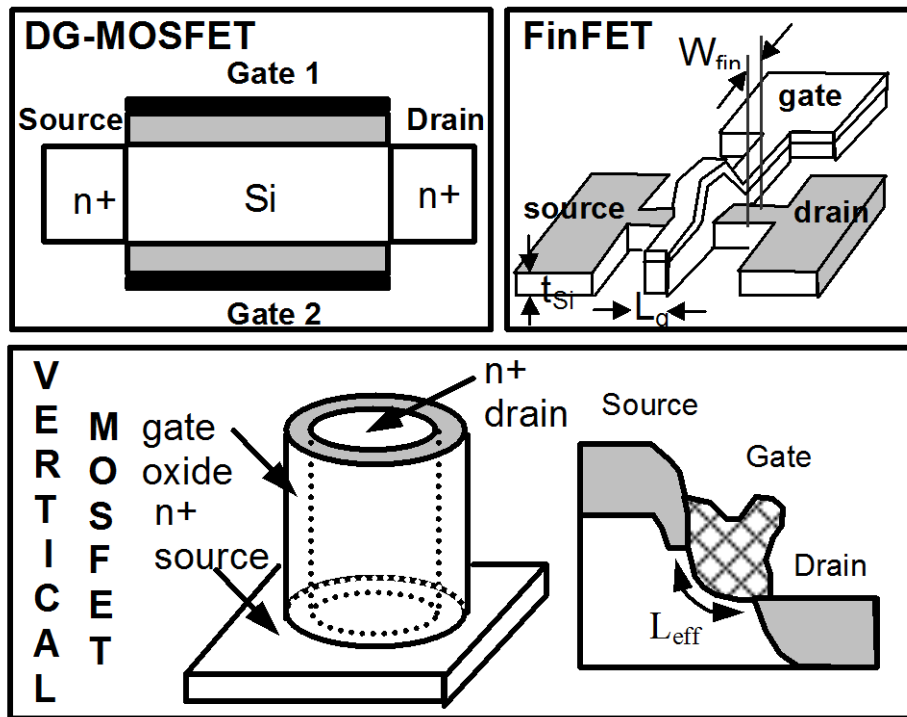


Intel's 15 nm channel length MOSFET

Emerging Device Architectures

● Double/Multi-Gate, FinFET and Nanowire MOSFETs

Better control of the channel charge (current) → overdrive



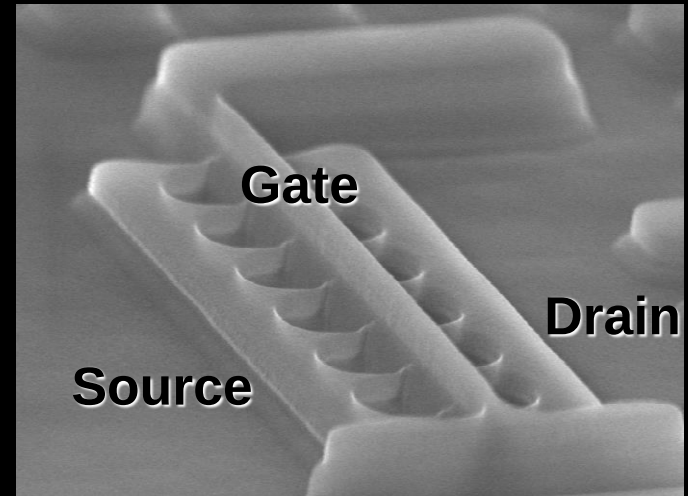
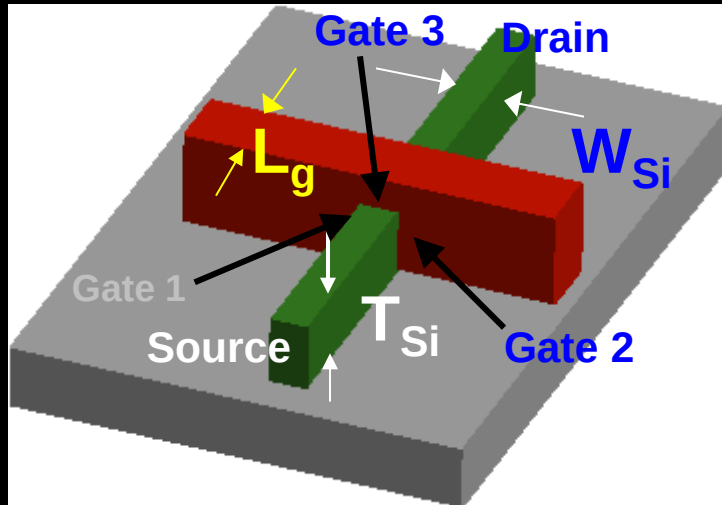
- excellent scalability: reduced SCE, V_T roll-off and DIBL
- better transconductance
- exploits SOI architecture

Both PMOS and NMOS up to 8nm shown

- lithography quasi-independent
- high level of functional integration

Tri-Gate and Multi-Fin Double Gate Devices

Tri-gate



Source: Intel

Improved short-channel effects
Higher ON current for lower SD Leakage

Identifying new parameters that may vary and impact circuit metrics

Where are we heading?

❑ **Emerging Materials/Devices for VLSI:**

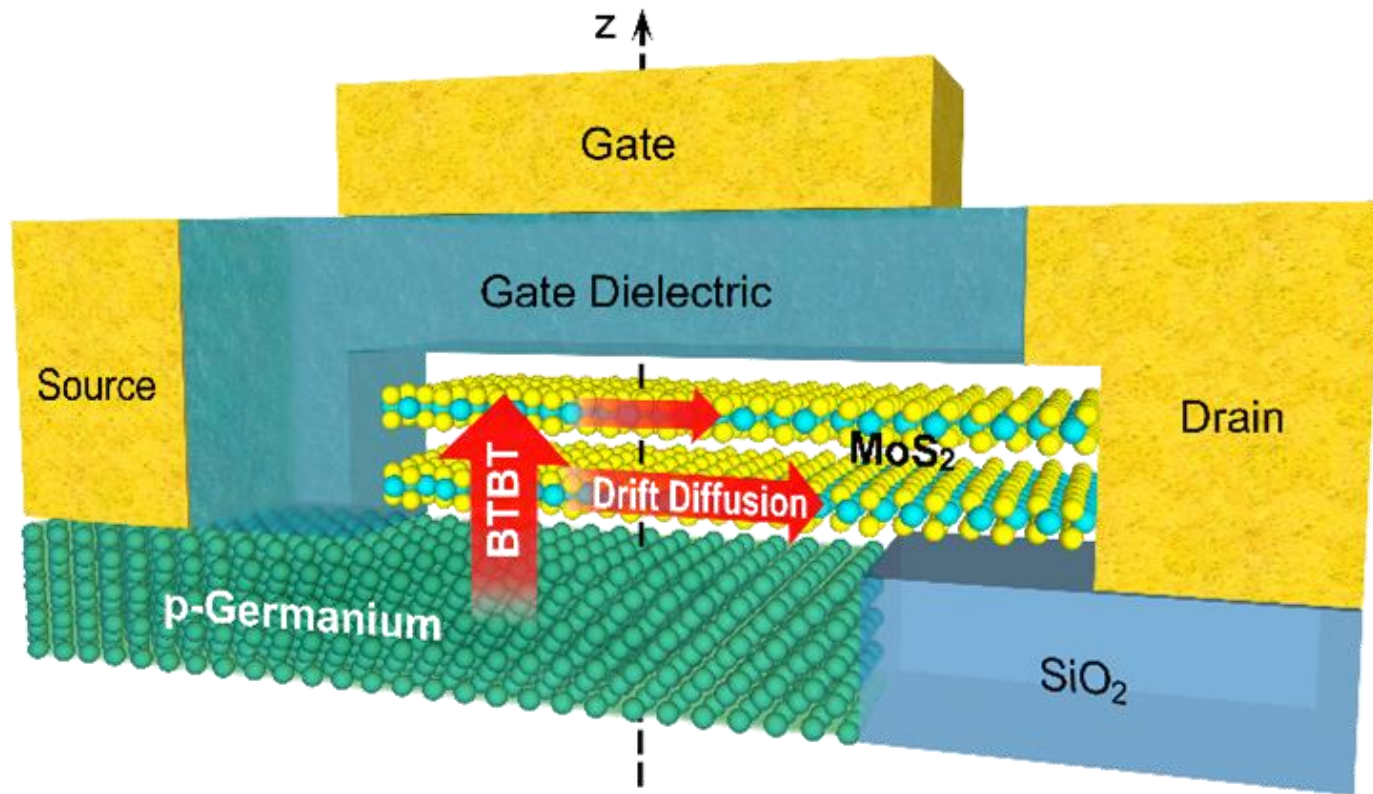
- Classical and non-classical CMOS
- 3-D ICs...alternative to scaling?
- Beyond Si (carbon nanotube, 2D materials: graphene, MoS₂ etc)
- Novel Interconnect Technologies
 - (CNT, Graphene Nanoribbons, RF, Optical, etc)

❑ **Green Electronics (Ultra Energy-Efficient)**

- Small Subthreshold Swing Devices (sub-kT/q devices)
 - Tunnel FETs
 - Gated Phase Change
 - Nano-electromechanical switches (NEMS)
 - Negative capacitance gate dielectrics
- Low Power Interconnects
- On-Chip Energy Storage (capacitive, inductive)
- Non-Von Neumann Architectures

ATLAS-TFET: Thinnest & Greenest Transistor

Nature, 526, 91-95, Oct 1, 2015.



ONLY Tunnel-FET to achieve subthermionic SS over four decades of drain current, at V_{DD} of 0.1 volts, with over 2X improvement in ON current.